

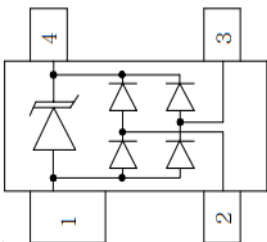
Features

- ◆ Ultra low capacitance: 0.6pF typical
- ◆ Ultra low leakage: nA level
- ◆ Low operating voltage: 5.0V
- ◆ Up to 2 data lines and one power line protects
- ◆ Low clamping voltage
- ◆ Complies with following standards:
 - ◆ – IEC 61000-4-2 (ESD) immunity test
Air : ±20kV; discharge: ±15kV
 - ◆ – IEC61000-4-5 (Lightning) 4A (8/20µs)
- ◆ SOT-143Package
- ◆ RoHS Compliant

Description

The ESDA5U0R0T4 is an ultra low capacitance TVS array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. ESDA5U0R0T4 has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into a 6-pin lead-free SOT-143 package. The combination of small size, ultra low capacitance, and high ESD surge capability make it ideal for use in applications such as multimedia, and other high speed ports.

Circuit Diagram



Applications

- ◆ USB 2.0
- ◆ Set-top box and Digital TV
- ◆ Video graphics cards
- ◆ Digital Video Interface (DVI)
- ◆ Notebook Computers
- ◆ PCI Express and Serial SATA Ports

Limiting Values($T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified)

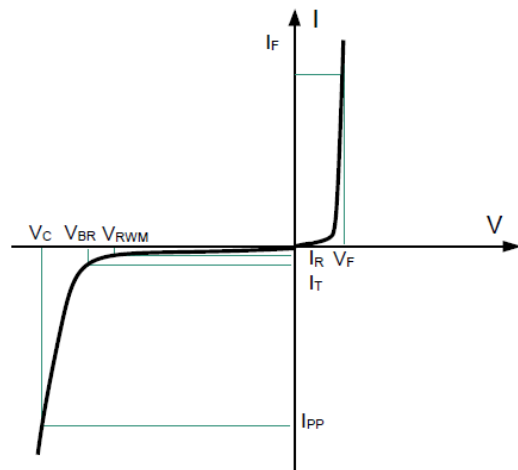
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs , I/O-GND)	Ppk	60	W
Peak Pulse Power (8/20 μs , Vcc-GND)	Ppk	270	W
Peak Pulse Current (8/20 μs , I/O-GND)	IPP	4.0	A
Peak Pulse Current (8/20 μs , Vcc-GND)	IPP	15.0	A
ESD per IEC 61000-4-2 (Air)	V _{ESD,VDD}	± 20	kV
ESD per IEC 61000-4-2 (Contact)	V _{ESD,I/O}	± 15	kV
Operating Temperature Range	TJ	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

Electrical Characteristics($T_A = 25\text{ }^\circ\text{C}$)

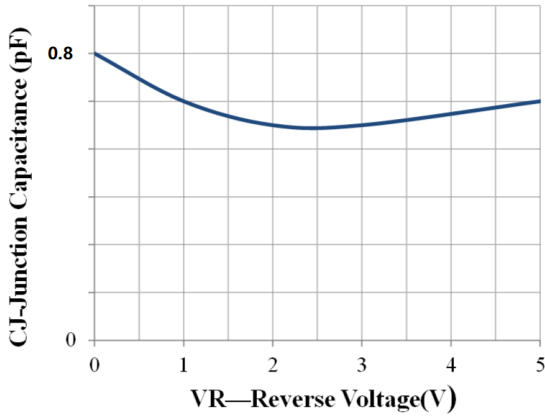
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}	Pin 5 to GND, I/O-GND			5.0	V
Breakdown Voltage	V _{BR}	I _T = 1mA, I/O-GND	6.5	7.4	8.0	V
Breakdown Voltage	V _{BR}	I _T = 1mA, I/O-I/O	7.0	8.3	9.0	V
Breakdown Voltage	V _{BR}	I _T = 1mA, VCC-GND	6.0	7.0	8.0	V
Reverse Leakage Current	I _R	V _{RWM} = 5V			0.1	μA
Clamping Voltage	V _C	I _{PP} = 1A (8 / 20 μs pulse), I/O-GND		8.0	12.0	V
Clamping Voltage	V _C	I _{PP} = 4A (8 / 20 μs pulse), I/O-GND		11.0	15.0	V
Clamping Voltage	V _C	I _{PP} = 1A (8 / 20 μs pulse), I/O-I/O		10.0	12.0	V
Clamping Voltage	V _C	I _{PP} = 4A (8 / 20 μs pulse), I/O-I/O		19.0	21.0	V
Clamping Voltage	V _C	I _{PP} = 1A (8 / 20 μs pulse), VCC-GND		7.5	9.0	V
Clamping Voltage	V _C	I _{PP} = 15A (8 / 20 μs pulse), VCC-GND			18.0	V
Junction Capacitance	C _J	V _R = 0V, f = 1MHz, I/O-GND		0.6	0.8	pF
Junction Capacitance	C _J	V _R = 0V, f = 1MHz, I/O-I/O		0.3	0.4	pF

Portion Electronics Parameter

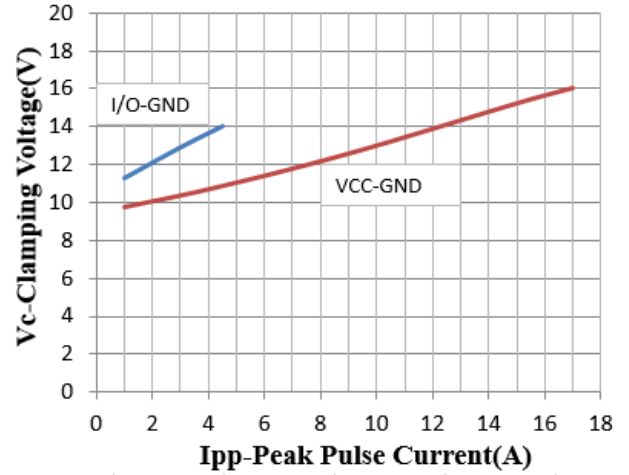
Symbol	Parameter
V _{RWM}	Peak Reverse Working Voltage
I _R	Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
I _{PP}	Maximum Reverse Peak Pulse Cur-
V _C	Clamping Voltage @ I _{PP}
V _F	Forward Voltage @ I _F



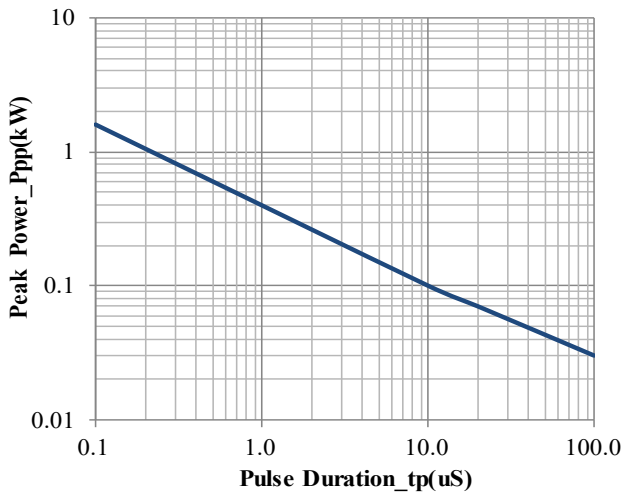
Typical Characteristics



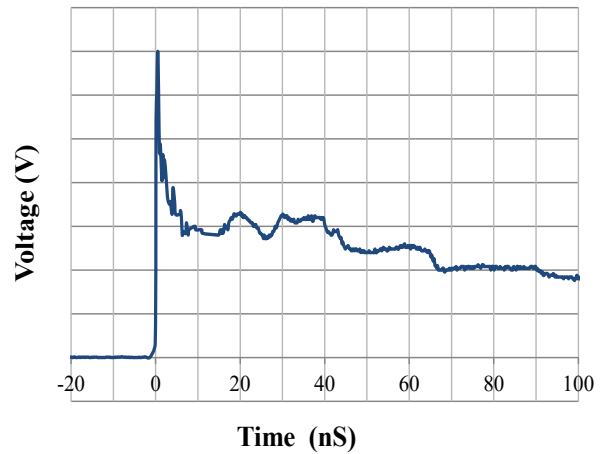
Junction Capacitance vs. Reverse Voltage



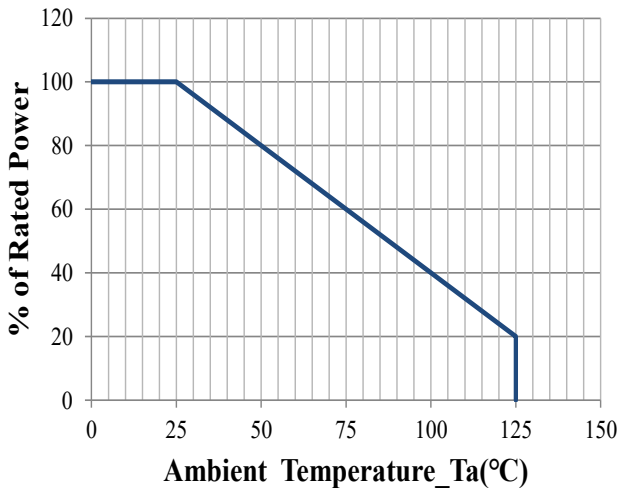
Clamping Voltage vs. Peak Pulse Current



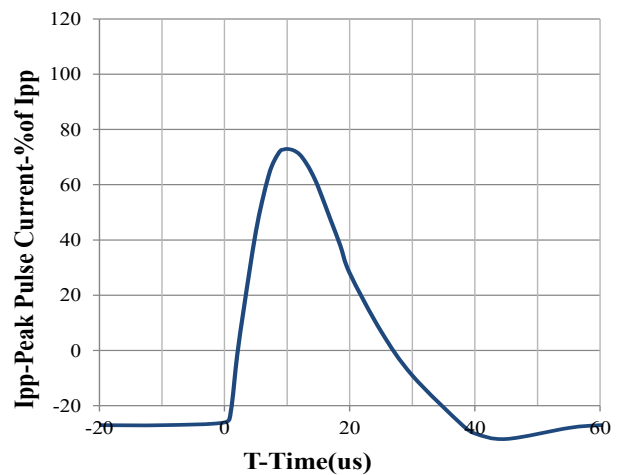
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform



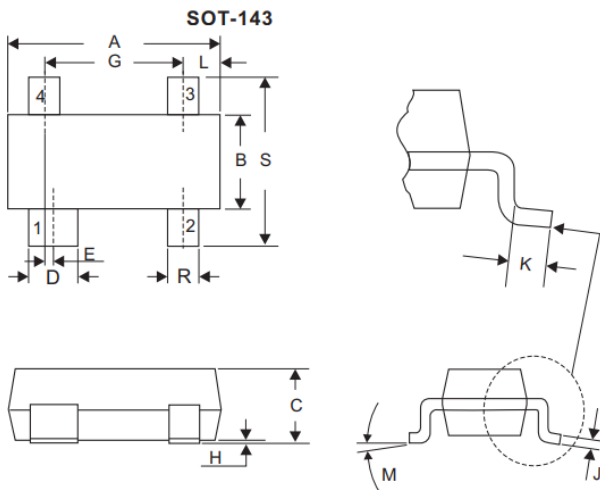
Power Derating Curve



8 / 20us Pulse Waveform

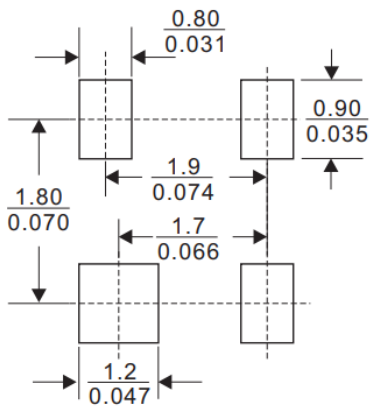
Package Dimension

SOT-143 Package Outline Drawing



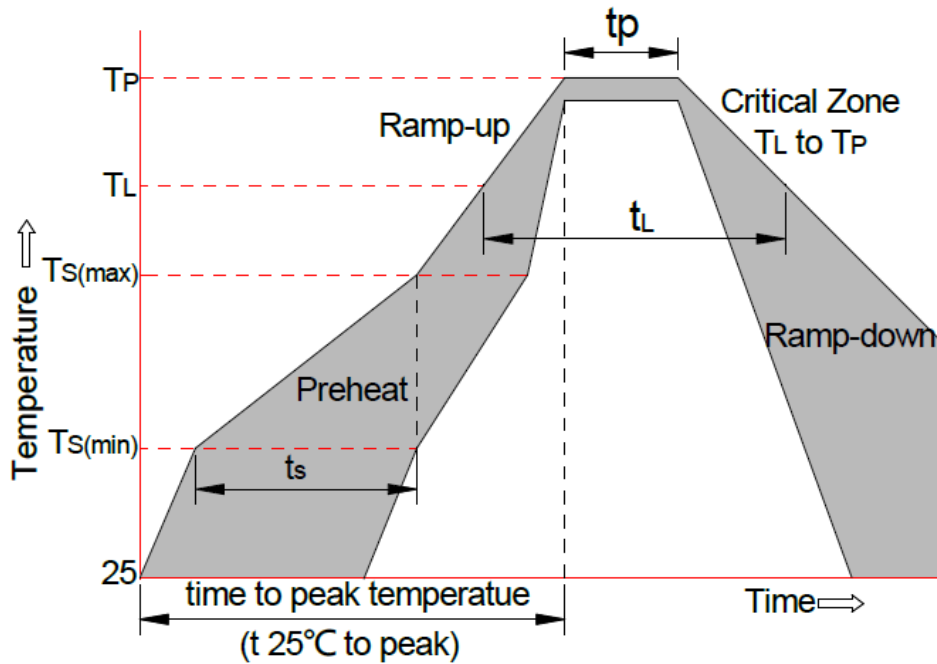
SYM	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.667	3.048	0.105	0.120
B	1.194	1.397	0.047	0.055
C	0.787	1.194	0.031	0.047
D	0.762	0.965	0.03	0.038
G	1.803	2.007	0.071	0.079
H	0.025	0.127	0.001	0.005
J	0.086	0.152	0.0034	0.006
K	0.102	0.305	0.004	0.012
L	0.45	0.6	0.018	0.024
M	0°	10°	0°	10°
R	0.356	0.559	0.014	0.022
S	2.083	2.489	0.082	0.098
E	0.2BSC		0.008 BSC	

Suggested Land Pattern



Dimensions in ($\frac{\text{millimeters}}{\text{inches}}$)

Soldering Parameters



Reflow Condition		Pb-Free Assembly
Pre-heat	-Temperature Min (Ts (min))	+150°C
	-Temperature Max (Ts (max))	+200°C
	-Time (Min to Max) (ts)	60-180 secs
Average ramp up rate(Liquid us Temp (TL) to peak)		3°C/sec. Max
Ts (max) to TL-Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature (TL) (Liquid us)	+217°C
	-Temperature (tL)	60-150 secs
Peak Temp (Tp)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (tp)		30 secs. Max
Ramp-down Rate		6 °C/secs. Max
xTime 25°C to Peak Temp (TP)		8 min. Max
Do not exceed		+260°C